

Bites		Search Text	DBs	Time Stamp	Δ
1	215	esd with buried	US-PGFUB; USPAI; 2004/09/17 EPO; JPO; DERMENT; 12:19	BR	
2	519	esd same ((under or below) with pad)	IRM.TDR US-PGFUB; USPAI; 2004/09/17 EPO; JPO; DERMENT; 12:19	BR	
3	91456	vias with resistance	IRM.TDR US-PGFUB; USPAI; 2004/09/17 EPO; JPO; DERMENT; 14:59	BR	
4	1857	vias with resistance with parallel	IRM.TDR US-PGFUB; USPAI; 2004/09/17 EPO; JPO; DERMENT; 15:38	BR	
5	9149	257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.	IRM.TDR US-PGFUB; USPAI; 2004/09/17 EPO; JPO; DERMENT; 15:39	BR	
6	255	esd and (resistance or resistor) and (transistor same below same pad)	IRM.TDR US-PGFUB; USPAI; 2004/09/17 EPO; JPO; DERMENT; 15:39	BR	
7	4145	257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.	IRM.TDR US-PGFUB; USPAI; 2004/09/17 EPO; JPO; DERMENT; 15:39	BR	
8	44	(257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried)	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
9	28	(257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried) and pad	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
10	16	((257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried)) not ((257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried) and pad)	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
11	55	(esd same ((under or below) with pad)) and (257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.)	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
12	53	((esd same ((under or below) with pad)) and (257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.)) not ((257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried) and pad)	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
13	59	(esd and (resistance or resistor) and (transistor same below same pad)) and (257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.)	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
14	5	(257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried) and &pd="20040817"	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
15	4	(257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried) and pad and &pd="20040817"	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
16	1	((257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried)) not ((257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried) and pad) and &pd="20040817"	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
17	6	(esd same ((under or below) with pad)) and (257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and &pd="20040817"	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
18	6	((esd same ((under or below) with pad)) and (257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.)) not ((257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and (esd with buried) and pad) and &pd="20040817"	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:09	BR	
19	6	(esd and (resistance or resistor) and (transistor same below same pad)) and (257/173,355.ccls. 361/90,91,91.1-91.8, FOR100.ccls.) and &pd="20040817"	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:10	BR	
20	14	514 515 516 517 518 519	IRM.TDR US-PGFUB; USPAI; 2005/01/12 EPO; JPO; DERMENT; 15:18	BR	
21	2	"6762466".pn.	IRM.TDR US-PGFUB; USPAI; 2005/06/30 EPO; JPO; DERMENT; 13:26	BR	
22	0	"10/759173"	IRM.TDR US-PGFUB; USPAI; 2005/06/30 EPO; JPO; DERMENT; 13:59	BR	

updated EAST 6/30/05